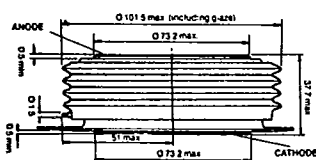


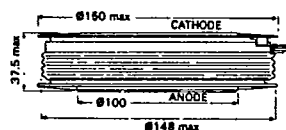
Series Type	Silicon Diameter	Repetitive Peak Voltages Available	Mean On-state Current at 180° half sine		RMS Current	Continuous On-state Current	Surge Current and Fusing at Max. T _J and 50% V _{RRM} 10mS Value		Rate of Rise of On-state Current Rise Time = 0.5μs			Rate of Rise of Off-state Voltage to 67% V _{DRM} T _J = 125°C	Peak Forward Gate Voltage	Peak Forward Gate Current	Peak Gate Power
	mm	V _{DRM} V _{RRM} V	I _{T(AV)} A	T _{HS} °C	I _{RMS} A	I _T A	I _{TSM} kA	I ² A²s	dI/dt A/μs	Gate source Ω V		dV/dt V/μs	V _{FGM} V	I _{FGM} A	P _{GM} W
BUTTON CAPSULE CONVERTER THYRISTOR															
DCR508	22	100-1200	295	55	465	400	3.3	54500	100	5	10	300	30	5	100
DCR504	22	100-1400	420	55	660	570	5.5	150000	100	5	10	200	30	10	100
DCR707	31	100-2400	500	55	785	710	5.6	157000	100	5	10	300	30	10	150
DCR818	38	2600-4200	500	55	850	780	6.0	180000	200	5	10	1600	30	10	100
DCR604	29.5	100-2100	580	55	910	780	7.5	281000	100	5	10	200	30	10	100
DCR703	31	100-1700	640	55	1000	900	7.5	281000	100	5	10	300	30	10	150
DCR601	29.5	100-1400	710	55	1115	925	9.5	451250	100	5	10	200	30	10	150
DCR806	38	100-2900	775	55	1220	1050	9.0	405000	100	5	10	300	30	10	150
DCR807															
DCR803	38	100-1700	900	55	1410	1200	11.2	625000	100	5	10	300	30	10	150
DCR804															
DCR1284	56	2400-3600	950	55	1490	1310	11.5	660000	150	5	10	300	30	10	150
DCR1278-755	56	2300-3800	1080	55	1695	1510	14.0	1350000	150	5	10	300	30	10	150
DCR1279	56	2700-4200	1100	55	1650	1550	12.0	720000	150	5	10	300	30	10	150
DCR1006	50	100-2900	1200	55	1880	1600	16.4	1350000	100	5	10	300	30	10	150
DCR1007															
DCR1277	50	2700-3600	1210	55	1900	1700	19.0	1800000	150	5	10	300	30	10	150
DCR1003	50	100-1700	1540	55	2420	2050	21.0	2205000	100	5	10	300	30	10	150
DCR1004															
DCR1275	56	600-2200	1540	55	2420	2100	24.0	2880000	150	5	10	300	30	10	100
DCR1274	56	100-1700	1680	55	2640	2200	27.0	3645000	150	5	10	300	30	10	150
DCR1478	75	3200-4200	1900	55	2990	2750	22.0	2420000	200	10	20	500	30	10	150
DCR1476	75	2300-3800	2100	55	3300	3000	29.0	4210000	150	5	10	500	30	10	150
DCR1475	75	800-2400	2850	55	4475	3950	40.0	8000000	200	5	10	500	30	10	150
DCR1474	75	100-1700	3350	55	5250	4550	49.0	12000000	150	5	10	500	30	10	150
DCR1675	100	4000-4800	3400	55	5340	4800	40.0	8000000	150	10	20	1000	30	30	150

All dimensions are in mm.

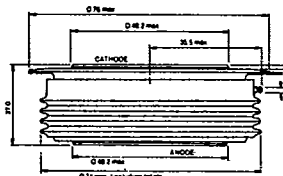


Weight = 1600 g
Minimum clamping force 38 kN
Maximum clamping force 47 kN

Y

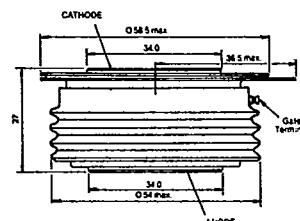


Weight = 3000 g
Minimum clamping force = 75 kN
Maximum clamping force = 90 kN

Z

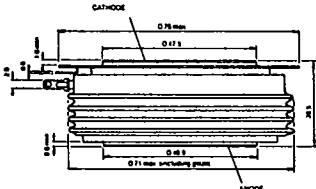
Weight = 500 g
Minimum clamping force: 18 kN
Maximum clamping force: 22 kN

F



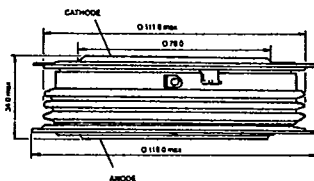
Weight 310 g
Minimum clamping force 9.5 kN
Maximum clamping force 12 kN

G



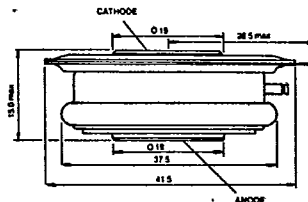
Weight 500 g
Minimum clamping force 20 kN
Maximum clamping force 24 kN

D



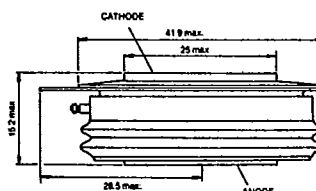
Weight = 1535 g
Minimum clamping force = 38 kN
Maximum clamping force = 47 kN

U



Weight Typ. 50 g
Minimum clamping force. 4.0 kN
Maximum clamping force. 5.5 kN

T

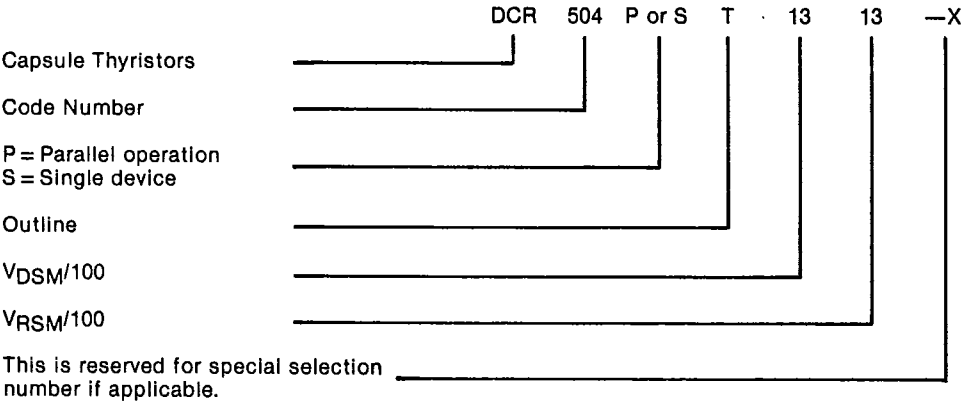


Weight (typical) 82 g
Minimum clamping force 5 kN
Maximum clamping force 9 kN

E

Gate Trigger Voltage V _{DWM} = 5V at 25°C	Gate Trigger Current V _{DWM} = 5V at 25°C	On-state Voltage at Peak Current at 25°C		Peak Off-state and Reverse Current at T _{vj}	Virtual Junction Temperature Off-state and Reverse	Thermal Resistance (2)				Factors needed for Power Loss calculations		Outline	Weight
						dc	180° Sinu-soidal	120° Rect-angular	Clamping Force				
V _{GT} V	I _{GT} mA	V _{TM} V	I _{TM} A	I _{RM} mA	T _{vj} °C	R _{th(j-h)} °C/W	R _{th(j-h)} °C/W	R _{th(jh)} °C/W	kN	V _o V	R _o Ω		g
3.5	150	1.6	450	30	125	0.11	0.12	0.14	4.5	0.97	0.00136	T	50
3.0	150	1.75	1000	30	125	0.083	0.093	0.113	4.5	1.05	0.0008	T	50
3.5	200	2.00	1000	50	125	0.052	0.058	0.068	9.0	1.15	0.001	G	310
4.0	400	3.375	1600	75	125	0.04	0.042	0.052	11.0	1.64	0.00151	G	310
3.0	150	1.625	1000	30	125	0.06	0.063	0.07	8.0	0.93	0.000667	E	82
3.5	200	1.50	1000	50	125	0.052	0.058	0.068	9.0	0.95	0.0006	G	310
3.0	150	1.3	1000	30	125	0.06	0.063	0.07	8.0	0.98	0.000328	E	82
3.5	200	1.875	1600	50	125	0.040	0.042	0.052	12.5	1.02	0.000497	G	310
		2.00								1.12	0.00053		
3.5	200	1.50	1600	50	125	0.040	0.042	0.052	12.5	0.91	0.000352	G	310
		1.675								0.96	0.00039		
4.0	400	2.75	2900	100	125	0.026	0.028	0.03	22.0	1.40	0.00053	D	500
4.0	400	2.3	2900	100	125	0.024	0.026	0.028	22.0	1.15	0.000481	D	500
4.0	400	2.40	2900	150	125	0.024	0.026	0.028	22.0	1.16	0.00048	D	500
3.5	200	1.875	2900	50	125	0.026	0.028	0.03	19.5	1.14	0.000243	F	500
		2.00								1.14	0.00031		
4.0	400	2.025	2900	100	125	0.024	0.026	0.028	22.0	0.95	0.00045	D	500
3.5	200	1.50	2900	50	125	0.026	0.028	0.03	19.5	0.90	0.000193	F	500
		1.625								0.87	0.00024		
4.0	400	1.625	2900	150	125	0.024	0.026	0.028	22.0	0.98	0.000202	D	500
4.0	400	1.42	2900	150	125	0.024	0.026	0.028	22.0	0.96	0.00016	D	500
4.0	400	2.10	2900	250	125	0.0115	0.0125	0.0132	43.0	1.40	0.00031	Y/U	1600/1535
4.0	400	1.875	2900	250	125	0.0115	0.0125	0.0132	43.0	1.03	0.00032	Y/U	1600/1535
4.0	400	1.5	2900	250	125	0.0115	0.0125	0.0132	43.0	1.00	0.000132	Y/U	1600/1535
4.0	400	1.30	2900	250	125	0.0115	0.0125	0.0132	43.0	0.92	0.00009	Y/U	1600/1535
3.5	500	1.45	2900	500	125	0.0085	0.0091	0.0097	83.0	1.00	0.00015	Z	2812

Nomenclature of High Power Thyristors



Notes:

(1) 100kg = 1kN

(2) Thermal resistance, R_{th}, is the value from junction to heatsink surface and includes contact thermal resistance.

$V_{DSM} = V_{DRM} + 100V$

$V_{RRM} = V_{RRM} + 100V$